

Wireless Bipolar Power Transistor 45W, 1930-1990 MHz

M/A-COM Products Released - Rev. 07.07

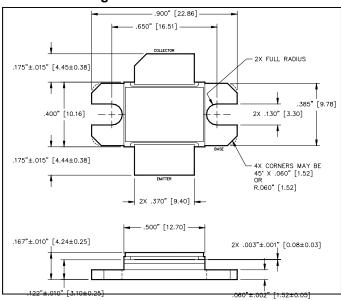
Features

- NPN silicon microwave power transistor
- Common emitter class AB operation
- Internal input and output impedance matching
- Diffused emitter ballasting
- Gold metallization system

ABSOLUTE MAXIMUM RATING AT 25°C

Parameter	Symbol	Rating	Units
Collector-Base Voltage	V_{CBO}	20	V
Collector-Emitter Voltage	V_{CES}	65	V
Emitter-Base Voltage	V _{EBO}	3.0	V
Collector Current	Ic	5.5	Α
Power Dissipation	P_D	100	W
Junction Temperature	TJ	200	°C
Storage Temperature	T _{STG}	-65 to + 150	°C
Thermal Resistance	θ_{JC}	1.3	°C/W

Outline Drawing



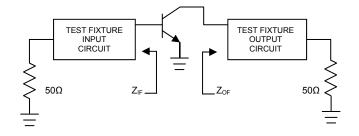
UNLESS OTHERWISE NOTED, TOLERANCES ARE INCHES $\pm .005$ " [MILLIMETERS ± 0.13 mm]

ELECTRICAL SPECIFICATIONS AT 25°C

Parameter	Symbol	Min	Max	Units	Test Conditions
Power Gain	G _P	8	-	dB	V _{CC} = 25V, I _{CQ} = 200 mA, P _{out} = 45 W, F =1930, 1990 MHz
Collector Efficiency	ŋc	40	-	%	V _{CC} = 25V, I _{CQ} = 200 mA, P _{out} = 45 W, F =1930, 1990 MHz
Input Return Loss	RL	10	-	dB	V _{CC} = 25V, I _{CQ} = 200 mA, P _{out} = 45 W, F =1930, 1990 MHz
Load Mismatch Tolerance	VSWR	-	3:1	-	V _{CC} = 25V, I _{CQ} = 200 mA, P _{out} = 45 W, F =1930, 1990 MHz

BROADBAND TEST FIXTURE IMPEDANCES

F (GHz)	Z _{IN} (Ω)	Z_{LOAD} (Ω)
1930	2.8-j5.5	4.8-j1.1
1960	2.7-j5.4	5.0-j1.3
1990	2.6-j5.3	5.2-j1.5



[•] **Europe** Tel: 44.1908.574.200 / Fax: 44.1908.574.300

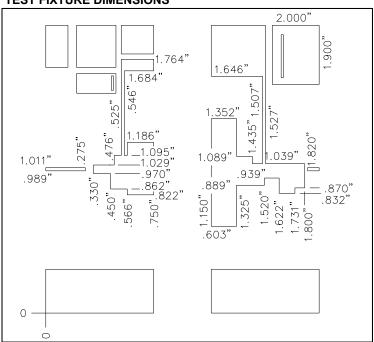
Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298
 Visit www.macomtech.com for additional data sheets and product information.



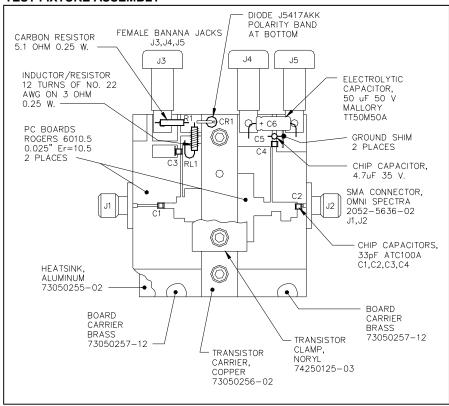
Wireless Bipolar Power Transistor 45W, 1930-1990 MHz

M/A-COM Products Released - Rev. 07.07

TEST FIXTURE DIMENSIONS



TEST FIXTURE ASSEMBLY



- North America Tel: 800.366.2266 / Fax: 978.366.2266
- Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300
- Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298
 Visit www.macomtech.com for additional data sheets and product information.